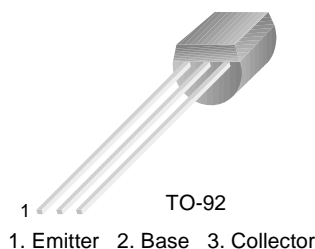


## 2N6517

### High Voltage Transistor

- Collector-Emitter Voltage:  $V_{CE0}=350V$
- Collector Dissipation:  $P_C$  (max)=625mW
- Complement to 2N6520
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



### NPN Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_a=25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	350	V
$V_{CEO}$	Collector-Emitter Voltage	350	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current	500	mA
$P_C$	Collector Power Dissipation	625	mW
$T_J$	Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature	-55 ~ 150	$^\circ C$

• Refer to 2N6515 for graphs

#### Electrical Characteristics $T_a=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CEO}$	* Collector-Emitter Breakdown Voltage	$I_C=1mA, I_B=0$	350			V
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C=100\mu A, I_E=0$	350			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\mu A, I_C=0$	6			V
$I_{CBO}$	Collector Cut-off Current	$V_{CB}=250V, I_E=0$			50	nA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB}=5V, I_C=0$			50	nA
$h_{FE}$	* DC Current Gain	$I_C=1mA, V_{CE}=10V$ $I_C=10mA, V_{CE}=10V$ $I_C=30mA, V_{CE}=10V$ $I_C=50mA, V_{CE}=10V$ $I_C=100mA, V_{CE}=10V$	20 30 30 20 15		200 200	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10mA, I_B=1mA$ $I_C=20mA, I_B=2mA$ $I_C=30mA, I_B=3mA$ $I_C=50mA, I_B=5mA$			0.3 0.35 0.5 1	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=10mA, I_B=1mA$ $I_C=20mA, I_B=2mA$ $I_C=30mA, I_B=3mA$			0.75 0.85 0.9	V
$C_{ob}$	Output Capacitance	$V_{CB}=20V, I_E=0, f=1MHz$			6	pF
$f_T$	* Current Gain Bandwidth Product	$I_C=10mA, V_{CE}=20V, f=20MHz$	40		200	MHz
$V_{BE(on)}$	Base Emitter On Voltage	$I_C=100mA, V_{CE}=10V$			2	V

\* Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$

# Package Dimensions

## TO-92



Dimensions in Millimeters

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